



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTY.'S DOCKET: 00 P 9031 US

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In re the application of: )  
Helmut Tews et al. ) Group Art: 2813  
Serial No.: 09/714,356 ) Examiner: Chen, Jack SJ.  
Filing Date: November 16, 2000 )  
Title: NITROGEN IMPLANTATION USING )  
A SHADOW EFFECT TO CONTROL )  
GATE OXIDE THICKNESS IN )  
DRAM SEMICONDUCTORS )

AMENDMENT UNDER 37 CFR \$1.115

Commissioner For Patents  
P.O. Box 1450  
Arlington, VA 22313-1450

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Sir:

In reply to the Office Action mailed March 11, 2003,  
which rejected the claims in the above-identified patent  
application, applicants respectfully request reconsideration  
based on the amendments hereinafter set forth.

IN THE CLAIMS:

SUB C17  
b1

1. (Twice Amended) In a process for forming dual  
gate oxides for use in high performance DRAM systems or  
logic circuits, the improvement comprising using a shadow  
area to control gate oxide thickness at active area (AA)  
corners adjacent a shallow trench isolation (STI) region,  
comprising:

I) a. forming an active area by depositing over a

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